

2SK3726-01MR

FUJI POWER MOSFET Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

(Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V _{DS}	450	V
Continuous drain current	I _D	±3	A
Pulsed drain current	I _D (puls)	±12	A
Gate-source voltage	V _{GS}	±30	V
Repetitive or non-repetitive	I _{AR} *2	3	A
Maximum Avalanche Energy	E _{AS} *1	92.8	mJ
Maximum Drain-Source dV/dt	dV _{DS} /dt *4	20	kV/μs
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/μs
Max. power dissipation	P _D	T _a =25°C	2.16
		T _c =25°C	17
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C
Isolation Voltage	V _{ISO} *6	2000	V _{rms}

*1 L=18.9mH, V_{CC}=45V, T_{ch}=25°C See to Avalanche Energy Graph *2 T_{ch} ≤ 150°C

*3 I_F ≤ -I_D, -di/dt=50A/μs, V_{CC} ≤ BV_{DSS}, T_{ch} ≤ 150°C *4 V_{DS} ≤ 450V *6 f=60Hz, t=60sec.

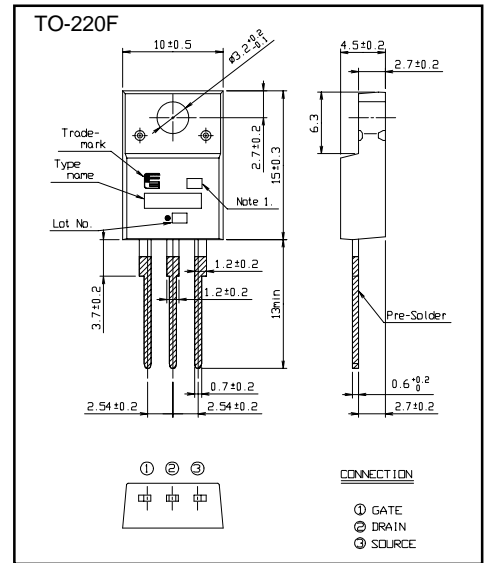
Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 250μA V _{GS} =0V	450			V
Gate threshold voltage	V _{GS(th)}	I _D = 250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =450V V _{GS} =0V			25	μA
		V _{DS} =360V V _{GS} =0V			250	
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V			100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =1.5A V _{GS} =10V		1.92	2.50	Ω
Forward transconductance	g _{fs}	I _D =1.5A V _{DS} =25V	1.25	2.5		S
Input capacitance	C _{iss}	V _{DS} =25V		235	355	pF
Output capacitance	C _{oss}	V _{GS} =0V		42	65	
Reverse transfer capacitance	C _{rss}	f=1MHz		2	3	
Turn-on time t _{on}	td(on)	V _{CC} =300V I _D =1.5A		16	24	ns
	t _r	V _{GS} =10V		4	6	
Turn-off time t _{off}	td(off)	R _{GS} =10 Ω		23	35	
	t _f			6	9	
Total Gate Charge	Q _G	V _{CC} =225V		10.5	16	nC
Gate-Source Charge	Q _{GS}	I _D =3A		5.5	8.3	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		1.0	1.5	
Avalanche capability	I _{AV}	L=18.9mH T _{ch} =25°C	3			A
Diode forward on-voltage	V _{SD}	I _F =3A V _{GS} =0V T _{ch} =25°C		1.00	1.50	V
Reverse recovery time	t _{rr}	I _F =3A V _{GS} =0V		0.28		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		1.4		μC

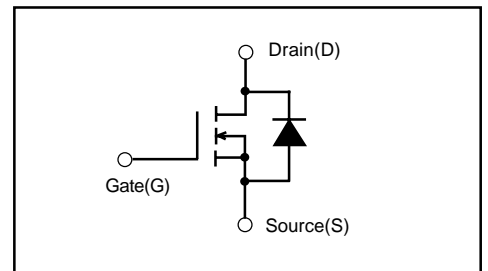
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			7.35	°C/W
	R _{th(ch-a)}	channel to ambient			58.0	°C/W

Outline Drawings [mm]



Equivalent circuit schematic



Characteristics

